1-Line, Bi-directional, Transient Voltage Suppressors

Descriptions

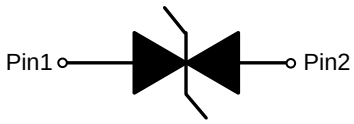
The ESD3V3B150TA is a bi-directional TVS (Transient Voltage Suppressor). It is specifically designed to protect sensitive electronic components that may be subjected to ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning. It is particularly well-suited for cellular phones, portable device, digital cameras, power supplies and many other portable applications because of its small package and low weight.

The ESD3V3B150TA may be used to provide ESD protection up to ±30kV air discharge ±30kV contact discharge. According to IEC61000-4-2, and withstand peak pulse current up to 9.0A (8/20μs) according to IEC61000-4-5.

The ESD3V3B150TA is available in SOD-523 package. Standard products are Pb-free and Halogen-free.



SOD-523



Circuit diagram

Features

- Stand-off voltage: ±3.3V Max
- Transient protection for each line according to
  IEC61000-4-2 (ESD): ±30kV air discharge ±30kV contact discharge
  IEC61000-4-4 (EFT): 40A (5/50ns)
  IEC61000-4-5 (surge): 9.0A (8/20μs)
- Solid-state silicon technology
- Low leakage current

Applications

- Cell phone handsets and accessories
- Personal Digital Assistants (PDAs)
- Notebooks, Desktops, and Serves
- Portable Instrumentation
- Digital Cameras
- MID/CAR DVD/MP3/MP4/PMP Players

Order information

Device	Marking	Package	Shipping
ESD3V3B150TA	eB	SOD-523	3000/Tape&Reel

Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Peak pulse current (t_p = 8/20μs)	I_{PP}	9.0	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	±30	kV
ESD according to IEC61000-4-2 contact discharge		±30	
Operation junction temperature	T_J	-55~150	°C
Lead temperature	T_L	260	°C
Storage temperature	T_{STG}	-55~150	°C

Electrical characteristics (TA=25°C ,unless otherwise noted)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				±3.3	V
Reverse leakage current	I_R	V_{RWM} = 3.3V			0.5	μA
Reveres breakdown voltage	V_{BR}	I_T=1mA	3.8	4.5	6.0	V
Clamping voltage	V_C	Ipp=1A tp=8/20us			7.0	V
		Ipp=9.0A tp=8/20us			10.0	V
Junction capacitance	C_J	V_R = 0V, f = 1MHz		10.0	20.0	pF

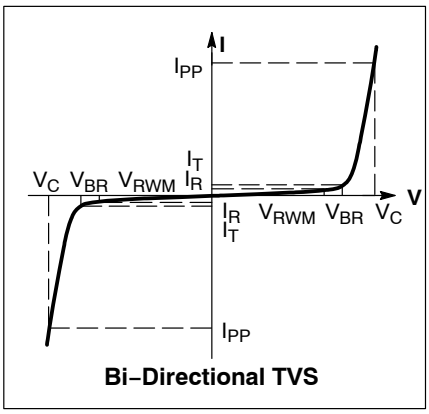
Electrical performance curve

V_C: Maximum clamping voltage

V_{br}: Reverse breakdown voltage

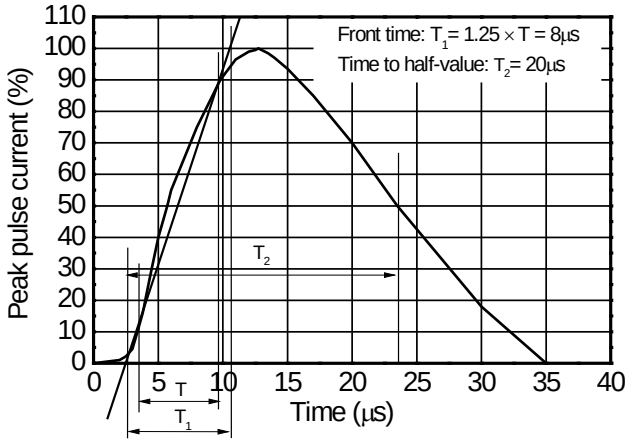
V_{RWM}: Working voltage

I_{PP}: Maximum peak current

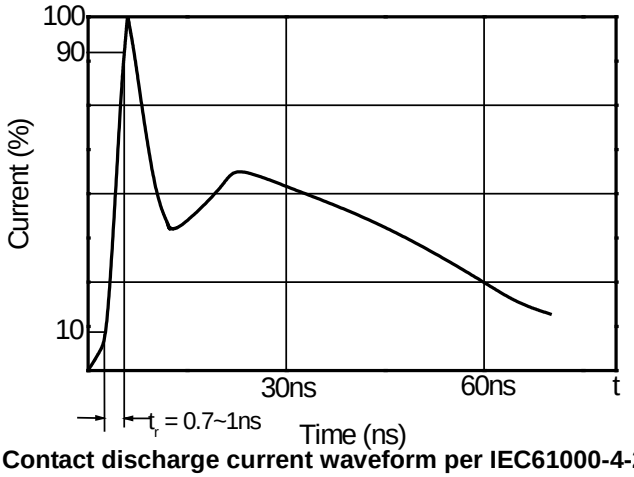


Bi-Directional TVS

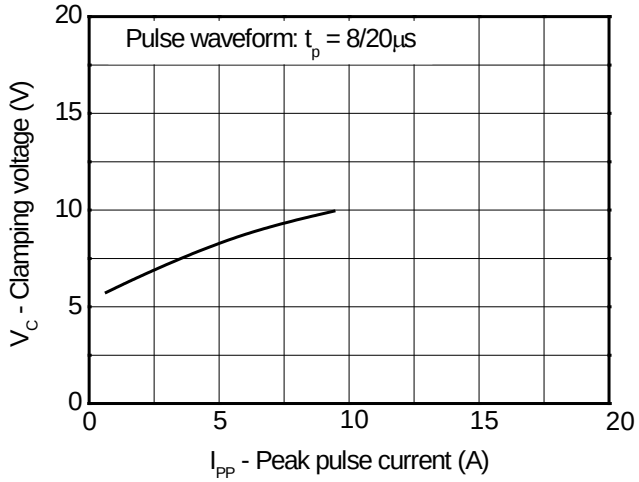
Typical characteristics (T_A=25°C, unless otherwise noted)



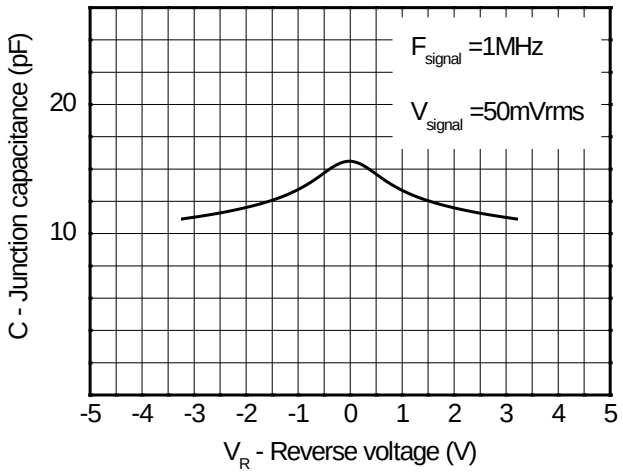
8/20μs waveform per IEC61000-4-5



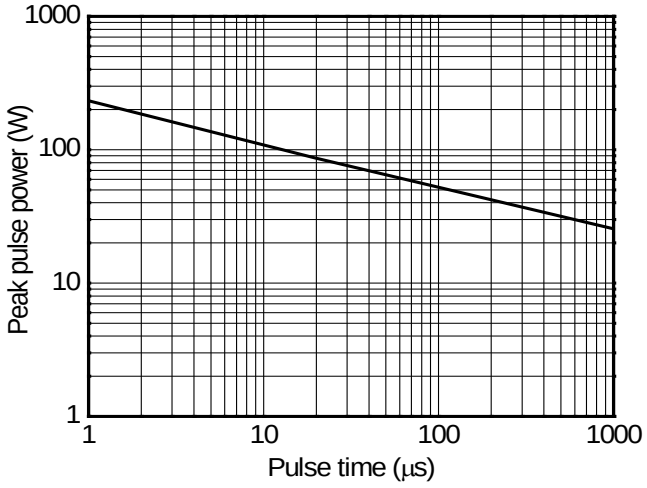
Contact discharge current waveform per IEC61000-4-2



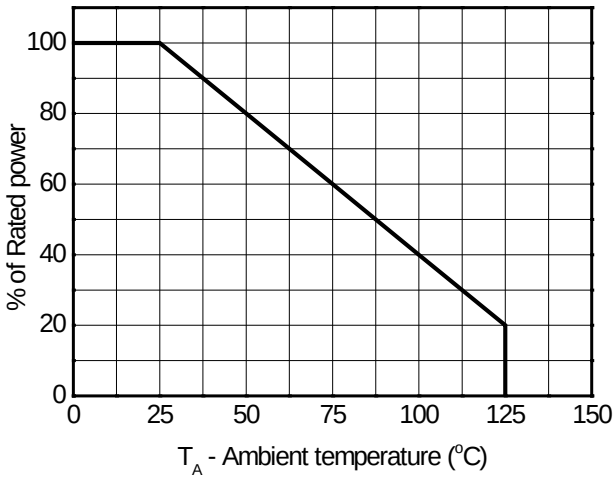
Clamping voltage vs. Peak pulse current



Capacitance vs. Reveres voltage

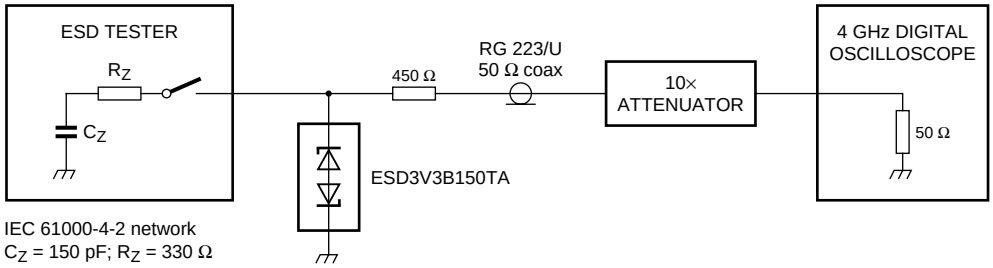


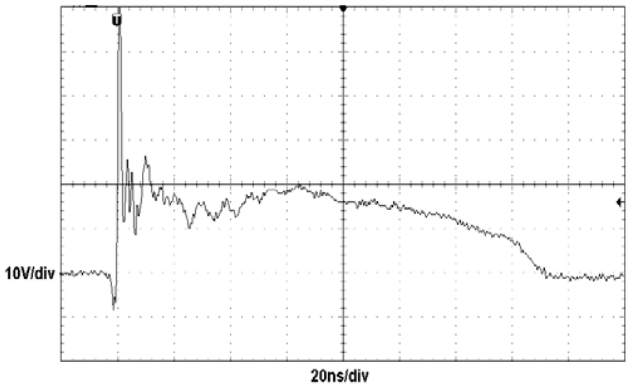
Non-repetitive peak pulse power vs. Pulse time



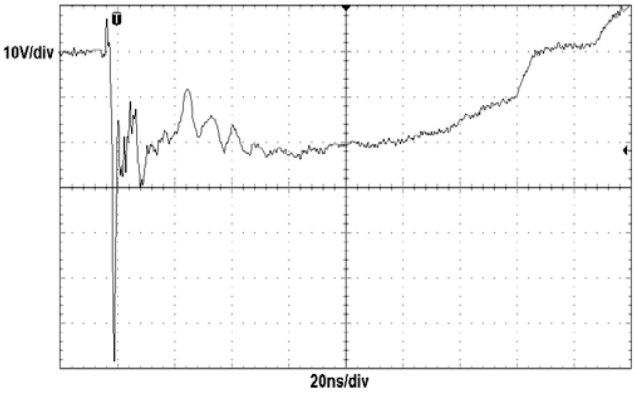
Power derating vs. Ambient temperature

ESD clamping test setup and waveforms





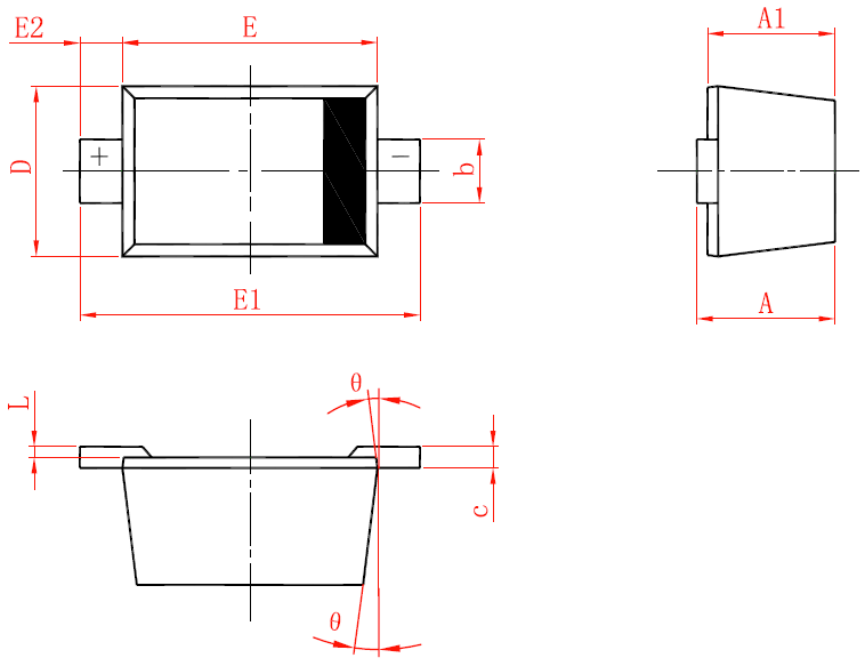
ESD clamping
(+8kV contact discharge per IEC61000-4-2)



ESD clamping
(-8kV contact discharge per IEC61000-4-2)

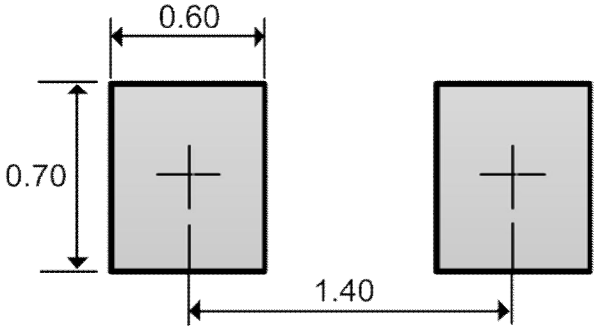
Package outline dimensions

SOD-523



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.510	0.640	0.770
A1	0.500	0.600	0.700
b	0.250	0.300	0.350
c	0.080	0.115	0.150
D	0.750	0.800	0.850
E	1.100	1.200	1.300
E1	1.500	1.600	1.700
E2	0.200 Ref		
L	0.010	0.040	0.070
θ	7° Ref		

Recommend land pattern (Unit: mm)



Note: This land pattern is for your reference only. Actual pad layouts may vary depending on application.